74HC423; 74HCT423

Dual retriggerable monostable multivibrator with reset

Rev. 6 — 19 December 2011

Product data sheet

1. General description

74HC423; 74HCT423 are high-speed Si-gate CMOS devices that are pin compatible with Low power Schottky TTL (LSTTL). They are specified in compliance with JEDEC standard no. 7A.

The 74HC423; 74HCT423 dual retriggerable monostable multivibrator with reset has two methods of output pulse width control.

- 1. The minimum pulse width is essentially determined by the selection of an external resistor (R_{EXT}) and capacitor (C_{EXT}), see Section 12.1.
- 2. Once triggered, the basic output pulse width may be extended by retriggering the gated active LOW-going edge input (nA) or the active HIGH-going edge input (nB). By repeating this process, the output pulse period (nQ = HIGH, nQ = LOW) can be made as long as desired. When nRD is LOW, it forces the nQ output LOW, the nQ output HIGH and also inhibits the triggering. Figure 10 and Figure 11 illustrate pulse control by reset.

The $n\overline{A}$ and nB inputs' Schmitt trigger action makes them highly tolerant to slower input rise and fall times.

The 74HC423; 74HCT423 are identical to the 74HC123; 74HCT123 except that they cannot be triggered via the reset input.

2. Features and benefits

- DC triggered from active HIGH or active LOW inputs
- Retriggerable for very long pulses up to 100 % duty factor
- Direct reset terminates output pulse
- Schmitt-trigger action on all inputs except for the reset input
- Complies with JEDEC standard no. 7A
- ESD protection:
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ♦ MM JESD22-A115-A exceeds 200 V
- Specified from −40 °C to +85 °C and from −40 °C to +125 °C

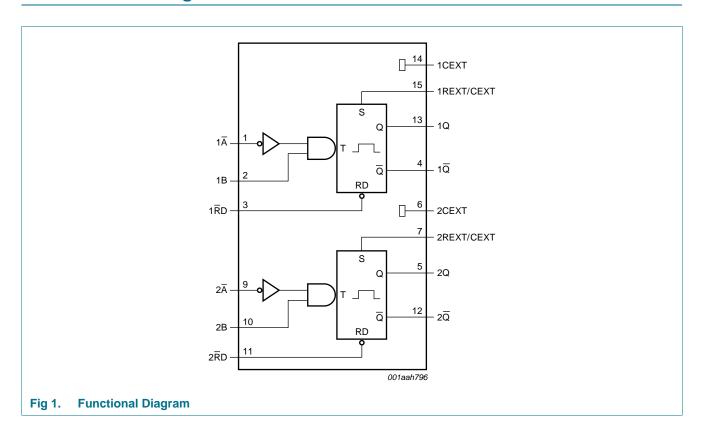


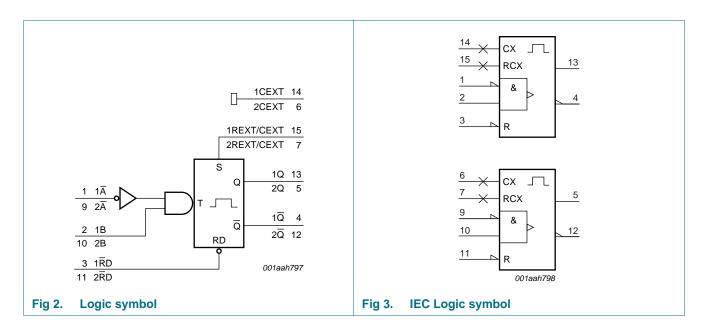
3. Ordering information

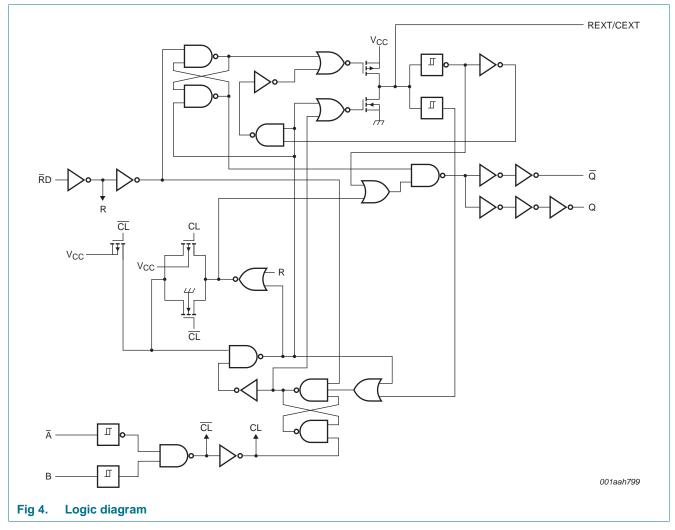
Table 1. Ordering information

Type number	Package									
	Temperature range	Name	Description	Version						
74HC423N	–40 °C to +125 °C	DIP16	plastic dual in-line package; 16 leads (300 mil)	SOT38-4						
74HCT423N										
74HC423D	C423D -40 °C to +125 °C		plastic small outline package; 16 leads;	SOT109-1						
74HCT423D	body width 3.9 mm									
74HC423BQ	–40 °C to +125 °C	DHVQFN16	plastic dual in-line compatible thermal enhanced very thin	SOT763-1						
74HCT423BQ			quad flat package; no leads; 16 terminals; body $2.5 \times 3.5 \times 0.85$ mm							
74HCT423DB	–40 °C to +125 °C	SSOP16	plastic shrink small outline package; 16 leads; body width 5.3 mm	SOT338-1						
74HCT423PW	–40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1						

4. Functional diagram

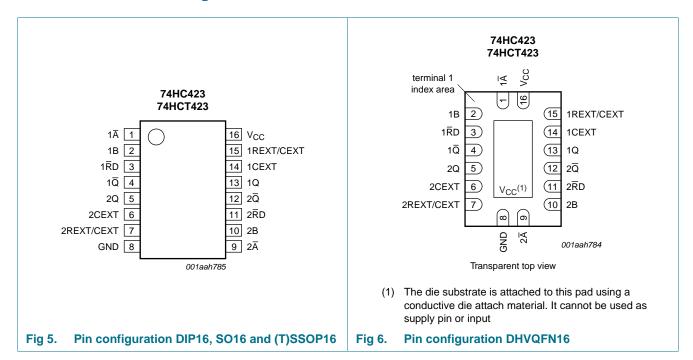






5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1 A , 2 A	1, 9	trigger input (negative edge triggered)
1B, 2B	2, 10	trigger input (positive edge triggered)
1RD, 2RD	3, 11	direct reset (active LOW)
1 Q , 2 Q	4, 12	output (active LOW)
GND	8	ground (0 V)
1Q, 2Q	13, 5	output (active HIGH)
1CEXT, 2CEXT	14, 6	external capacitor connection
1REXT/CEXT, 2REXT/CEXT	15, 7	external resistor/capacitor connection
V _{CC}	16	supply voltage

6. Functional description

Table 3. Function table[1]

Input nRD			Output	
nRD	nΑ	nB	nQ	nQ
L	X	X	L	Н
X	Н	X	<u>[2]</u>	H[2]
X	X	L	<u>[2]</u>	H[2]
Н	L	\uparrow	Л	Ъ
Н	\	Н	Л	T

^[1] H = HIGH voltage level;

L = LOW voltage level;

X = don't care;

↑ = LOW-to-HIGH transition;

 \downarrow = HIGH-to-LOW transition;

= one HIGH level output pulse;

= one LOW level output pulse.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7	V
I _{IK}	input clamping current	$V_{I} < -0.5 \text{ V or } V_{I} > V_{CC} + 0.5 \text{ V}$	<u>[1]</u> -	±20	mA
I _{OK}	output clamping current	$V_O < -0.5 \text{ V or } V_O > V_{CC} + 0.5 \text{ V}$	<u>[1]</u> -	±20	mA
Io	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±25	mA
I _{CC}	supply current		-	50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	DIP16 package	[2] _	750	mW
		SO16, SSOP16, TSSOP16 and DHVQFN16 packages	<u>[3]</u> _	500	mW

^[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

^[2] If the monostable multivibrator was triggered before this condition was established, the pulse will continue as programmed.

^[2] For DIP16 packages: above 70 $^{\circ}\text{C}$ the value of P_{tot} derates linearly at 12 mW/K.

^[3] For SO16 packages: above 70 °C the value of P_{tot} derates linearly at 8 mW/K; For SSOP16 and TSSOP16 packages: above 60 °C the value of P_{tot} derates linearly at 5.5 mW/K; For DHVQFN16 packages: above 60 °C the value of P_{tot} derates linearly at 4.5 mW/K.

Recommended operating conditions

Table 5. **Recommended operating conditions**

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	tions 74HC423			7	Unit		
			Min	Тур	Max	Min	Тур	Max	
V_{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	V_{CC}	0	-	V_{CC}	V
Vo	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T _{amb}	ambient temperature		-40	-	+125	-40	-	+125	°C
$\Delta t/\Delta V$	input transition rise	$V_{CC} = 2.0 \text{ V}$	-	-	625	-	-	-	ns/V
	and fall rate	V _{CC} = 4.5 V	-	1.67	139	-	1.67	139	ns/V
		$V_{CC} = 6.0 \text{ V}$	-	-	83	-	-	-	ns/V

Static characteristics

Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C		–40 °C to +85 °C		–40 °C to +125 °C		Unit	
			Min	Тур	Max	Min	Max	Min	Max	
74HC423	'		'	•			•	'		
V_{IH}	HIGH-level	$V_{CC} = 2.0 \text{ V}$	1.5	1.2	-	1.5	-	1.5	-	V
	input voltage	V _{CC} = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		$V_{CC} = 6.0 \text{ V}$	4.2	3.2	-	4.2	-	4.2	-	V
V _{IL}	LOW-level	$V_{CC} = 2.0 \text{ V}$	-	8.0	0.5	-	0.5	-	0.5	V
input voltage		V _{CC} = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		$V_{CC} = 6.0 \text{ V}$	-	2.8	1.8	-	1.8	-	1.8	V
V_{OH}	HIGH-level	$V_I = V_{IH}$ or V_{IL}								
output vol	output voltage	$I_{O} = -20 \mu A; V_{CC} = 2.0 V$	1.9	2.0	-	1.9	-	1.9	-	V
		$I_{O} = -20 \mu A; V_{CC} = 4.5 V$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -20 \mu A; V_{CC} = 6.0 V$	5.9	6.0	-	5.9	-	5.9	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.98	4.32	-	3.84	-	3.7	-	V
		$I_{O} = -5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.48	5.81	-	5.34	-	5.2	-	V
V_{OL}	LOW-level	$V_I = V_{IH}$ or V_{IL}								
	output voltage	$I_O = 20 \mu A; V_{CC} = 2.0 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 6.0 \text{ V}$	-	0	0.1	-	0.1	-	0.1	V
		$I_{O} = 4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.15	0.26	-	0.33	-	0.4	V
		$I_{O} = 5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.26	-	0.33	-	0.4	V
l _l	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	±0.1	-	±1.0	-	±1.0	μΑ
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0 \text{ V}$	-	-	8.0	-	80	-	160	μА

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 Table 6.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	Min	Max	
C_{I}	input capacitance		-	3.5	-	-	-	-	-	pF
74HCT42	3									
V_{IH}	HIGH-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	2.0	1.6	-	2.0	-	2.0	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	1.2	8.0	-	8.0	-	8.0	V
V _{OH}	HIGH-level	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	$I_{O} = -20 \mu A$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -4.0 \text{ mA}$	3.98	4.32	-	3.84	-	3.7	-	V
V_{OL}		$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$								
	voltage	I _O = 20 μA	-	0	0.1	-	0.1	-	0.1	V
		$I_{O} = 4.0 \text{ mA}$	-	0.15	0.26	-	0.33	-	0.4	V
l _l	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	±0.1	-	±1.0	-	±1.0	μΑ
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$; $I_O = 0 \text{ A}$	-	-	8.0	-	80	-	160	μА
ΔI_{CC}	additional supply current	per input pin; $V_I = V_{CC} - 2.1 \text{ V}$; other inputs at V_{CC} or GND; $V_{CC} = 4.5 \text{ V}$ to 5.5 V; $I_O = 0 \text{ A}$								
		nĀ, nB inputs	-	35	126	-	158	-	172	μΑ
		nRD input	-	50	180	-	225	-	245	μΑ
Cı	input capacitance		-	3.5	-	-	-	-	-	pF

10. Dynamic characteristics

Table 7. Dynamic characteristics GND = 0 *V; test circuit see Figure 12.*

Symbol	Parameter	Conditions			25 °C			°C to 5 °C		°C to 5 °C	Uni
				Min	Тур	Max	Min	Max	Min	Max	
74HC42	3					'					
t _{pd}	propagation delay	$n\overline{A}$ or nB to nQ or $n\overline{Q}$; $R_{EXT} = 5 k\Omega$; $C_{EXT} = 0 pF$; see Figure 7	[1]								
		V _{CC} = 2.0 V		-	80	255	-	320	-	385	ns
		V _{CC} = 4.5 V		-	29	51	-	64	-	77	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		-	25	-	-	-	-	-	ns
		V _{CC} = 6.0 V		-	23	43	-	54	-	65	ns
		nRD to nQ or nQ; see Figure 7	[1]								
		V _{CC} = 2.0 V		-	66	215	-	270	-	325	ns
		V _{CC} = 4.5 V		-	24	43	-	54	-	65	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		-	20	-	-	-	-	-	ns
		V _{CC} = 6.0 V		-	19	37	-	46	-	55	ns
t _t	transition time	see Figure 7	[2]								
		V _{CC} = 2.0 V		-	19	75	-	95	-	110	ns
		V _{CC} = 4.5 V		-	7	15	-	19	-	22	ns
		V _{CC} = 6.0 V		-	6	13	-	16	-	19	ns
t _W	pulse width	nA input LOW; see Figure 7 and Figure 8									
		V _{CC} = 2.0 V		100	11	-	125	-	150	-	ns
		V _{CC} = 4.5 V		20	4	-	25	-	30	-	ns
		V _{CC} = 6.0 V		17	3	-	21	-	26	-	ns
		nB input HIGH; see Figure 7 and Figure 8									
		V _{CC} = 2.0 V		100	17	-	125	-	150	-	ns
		V _{CC} = 4.5 V		20	6	-	25	-	30	-	ns
		V _{CC} = 6.0 V		17	5	-	21	-	26	-	ns
		nRD input LOW; see Figure 7 and Figure 8									
		V _{CC} = 2.0 V		100	14	-	125	-	150	-	ns
		V _{CC} = 4.5 V		20	5	-	25	-	30	-	ns
		V _{CC} = 6.0 V		17	4	-	21	-	26	-	ns
		nQ HIGH or n \overline{Q} LOW; V _{CC} = 5.0 V; R _{EXT} = 10 kΩ; C _{EXT} = 100 nF; see Figure 7 and Figure 8		-	450	-	-	-	-	-	μS
		nQ HIGH or n \overline{Q} LOW; V _{CC} = 5.0 V; R _{EXT} = 5 k Ω ; C _{EXT} = 0 pF; V _I = GND to V _{CC} ; see Figure 7 and Figure 8	[3]	-	75	-	-	-	-	-	ns
t _{rtrig}	retrigger time	$n\overline{A}$ or nB input; V_{CC} = 5.0 V; R_{EXT} = 5 k Ω ; C_{EXT} = 0 pF; see <u>Figure 10</u>	<u>[4]</u>	-	110	-	-	-	-	-	ns

Table 7. Dynamic characteristics ...continued GND = 0 V; test circuit see Figure 12.

Symbol	Parameter	Conditions			25 °C			-40 °C to +85 °C		°C to 5 °C	Unit
				Min	Тур	Max	Min	Max	Min	Max	
R_{EXT}	external timing	V _{CC} = 2.0 V; see Figure 8		10	-	1000	-	-	-	-	kΩ
	resistor	V _{CC} = 5.0 V		2	-	1000	-	-	-	-	$k\Omega$
C_{EXT}	external timing capacitor	V _{CC} = 5.0 V; see <u>Figure 8</u>	<u>[5]</u>			no	o limits	3			pF
C_{PD}	power dissipation capacitance	per package; $V_I = GND$ to V_{CC}	[6]	-	54	-	-	-	-	-	pF
74HCT42	23										
t _{pd}	propagation delay	$n\overline{A}$ or nB to nQ or $n\overline{Q}$; $R_{EXT} = 5 k\Omega$; $C_{EXT} = 0 pF$; see Figure 7									
		V _{CC} = 4.5 V	[1]	-	30	51	-	64	-	77	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$	[1]	-	26	-	-	-	-	-	ns
		\overline{RD} to \overline{RD} to \overline{RD} ; $\overline{REXT} = 5$ kΩ; $\overline{REXT} = 0$ pF; see Figure 7	[1]	-	26	48	-	60	-	72	ns
		V _{CC} = 4.5 V	[1]	-	26	48	-	60	-	72	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$	[1]	-	22	-	-	-	-	-	ns
t _t	transition time	V _{CC} = 4.5 V; <u>Figure 7</u>	[2]	-	7	15	-	19	-	22	ns
t _W	pulse width	trigger pulse; $n\overline{A}$ input LOW; $V_{CC} = 4.5 \text{ V}$; see Figure 7 and Figure 10		20	5	-	25	-	30	-	ns
		trigger pulse; nB input HIGH; $V_{CC} = 4.5 \text{ V}$; see Figure 7 and Figure 10		20	5	-	25	-	30	-	ns
		reset pulse; \overline{nRD} input LOW; $V_{CC} = 4.5$ V; see Figure 7 and Figure 11		20	7	-	25	-	30	-	ns
		output pulse; nQ HIGH or n \overline{Q} LOW; V_{CC} = 5.0 V; R_{EXT} = 10 k Ω ; C_{EXT} = 100 nF; see Figure 7, Figure 10 and Figure 11		-	450	-	-	-	-	-	μS
		output pulse; nQ HIGH or $n\overline{Q}$ LOW; V_{CC} = 5.0 V; R_{EXT} = 5 k Ω ; C_{EXT} = 0 pF; V_I = GND to V_{CC} – 1.5 V; see <u>Figure 7</u> , <u>Figure 10</u> and <u>Figure 11</u>	[3]	-	75	-	-	-	-	-	ns
t _{rtrig}	retrigger time	$n\overline{A}$ or nB input; V_{CC} = 5.0 V; R_{EXT} = 5 k Ω ; C_{EXT} = 0 pF; see Figure 10		-	110	-	-	-	-	-	ns
R _{EXT}	external timing resistor	V _{CC} = 5.0 V; see <u>Figure 8</u>		2	-	1000	-	-	-	-	kΩ
C _{EXT}	external timing capacitor	V _{CC} = 5.0 V; see <u>Figure 8</u>	<u>[5]</u>			no	o limits	3			pF

Table 7. Dynamic characteristics ...continued

GND = 0 V; test circuit see Figure 12.

Symbol	Parameter	Conditions	25 °C						Unit	
			Min	Тур	Max	Min	Max	Min	Max	
C_{PD}	power dissipation capacitance	per package; $V_1 = GND$ to $V_{CC} - 1.5 V$ [6]	-	56	-	-	-	-	-	pF

- [1] t_{pd} is the same as t_{PHL} and t_{PLH} .
- [2] t_t is the same as t_{THL} and t_{TLH} .
- [3] For other R_{EXT} and C_{EXT} combinations see Figure 8. If $C_{EXT} > 10$ pF, the next formula is valid:

 $t_W = K \times R_{EXT} \times C_{EXT}$ (typ.), where:

t_W = output pulse width in ns;

 R_{EXT} = external resistor in $k\Omega$;

C_{EXT} = external capacitor in pF;

K = 0.55 for $V_{CC} = 2.0$ V and 0.45 for $V_{CC} = 5.0$ V; see Figure 9.

Inherent test jig and pin capacitance at pins 15 and 7 (nREXT/CEXT) is 7 pF.

[4] The time to retrigger the monostable multivibrator depends on the values of R_{EXT} and C_{EXT}. The output pulse width will only be extended when the time between the active-going edges of the trigger input pulses meets the minimum retrigger time.

If $C_{EXT} > 10$ pF, the next formula (at $V_{CC} = 5.0$ V) for the set-up time of a retrigger pulse is valid:

$$t_{rtrig} = 30 + 0.19 \times R_{EXT} \times C_{EXT}^{0.9} + 13 \times R_{EXT}^{1.05}$$
 (typ.); where:

 t_{rtrig} = retrigger time in ns;

C_{EXT} = external capacitor in pF;

 R_{EXT} = external resistor in $k\Omega$.

Inherent test jig and pin capacitance at pins 15 and 7 (nREXT/CEXT) is 7 pF.

- [5] When the device is powered-up, initiate the device via a reset pulse, when C_{EXT} < 50 pF.
- [6] C_{PD} is used to determine the dynamic power dissipation (P_D in μW):

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o)$$
; where:

f_i = input frequency in MHz;

 f_0 = output frequency in MHz;

C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

11. Waveforms

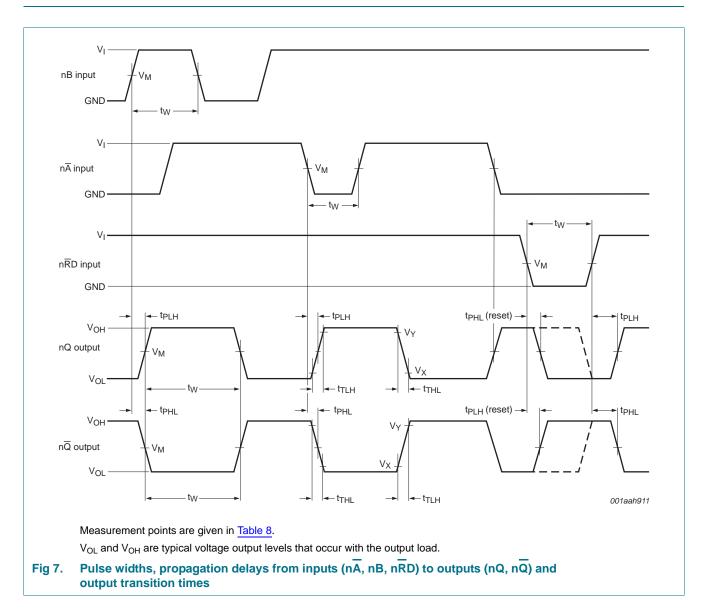
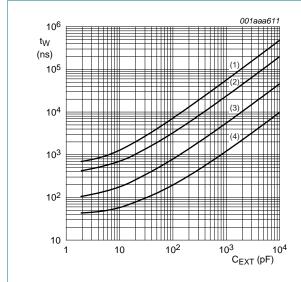


Table 8. Measurement points

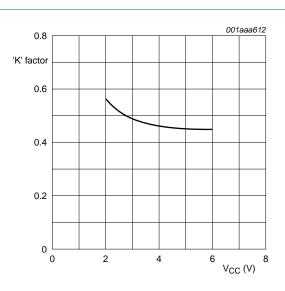
Туре	Input		Output					
	V _I	V _M	V _M	V _X	V _Y			
74HC423	V _{CC}	0.5V _{CC}	0.5V _{CC}	0.1V _{CC}	0.9V _{CC}			
74HCT423	3 V	1.3 V	1.3 V	0.1V _{CC}	0.9V _{CC}			



 V_{CC} = 5.0 V and T_{amb} = 25 °C.

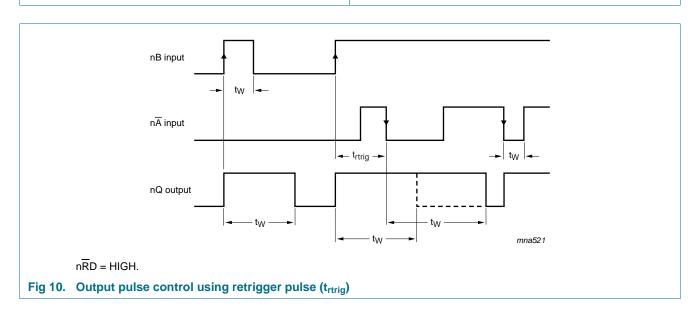
- (1) $R_{EXT} = 100 \text{ k}\Omega$.
- (2) $R_{EXT} = 50 \text{ k}\Omega$.
- (3) $R_{EXT} = 10 kΩ$.
- (4) $R_{EXT} = 2 k\Omega$.

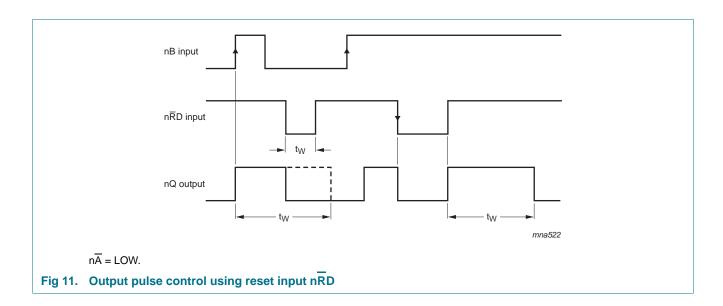
Fig 8. Typical output pulse width as a function of the external capacitor values

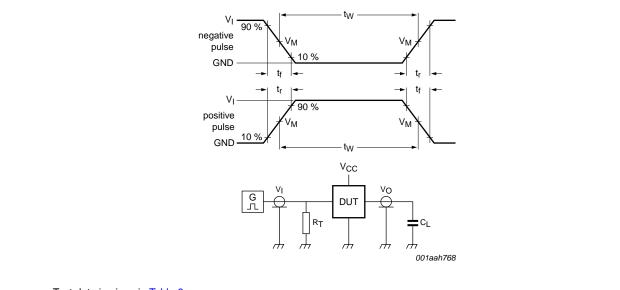


External capacitance = 10 nF, external resistance = 10 k Ω to 100 k Ω and T_{amb} = 25 °C.

Fig 9. Typical 'K' factor







Test data is given in Table 9.

Definitions for test circuit:

 $R_{T} = \mbox{Termination}$ resistance should be equal to output impedance Z_{0} of the pulse generator.

 C_L = Load capacitance including jig and probe capacitance.

Fig 12. Test circuit for measuring switching times

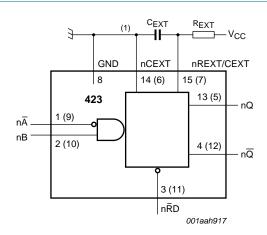
Table 9. Test data

Supply	Input	put			
V _{CC}	V _I	t _r , t _f	CL		
2.0 V to 6.0 V	V _{CC}	6 ns	15 pF, 50 pF		

12. Application information

12.1 Timing component connections

The basic output pulse width is essentially determined by the values of the external timing components R_{EXT} and C_{EXT} .



(1) For minimum noise generation it is recommended that the nCEXT pins (6, 14) are connected to ground externally to the GND pin (8).

Fig 13. Timing component connections

12.1.1 Minimum monostable pulse width

To set the minimum pulse width, when $C_{EXT} < 10$ nF, see Figure 8 and when $C_{EXT} > 10$ nF, the output pulse width is defined as:

 $t_W = 0.45 \times R_{EXT} \times C_{EXT}$ (typ.), where:

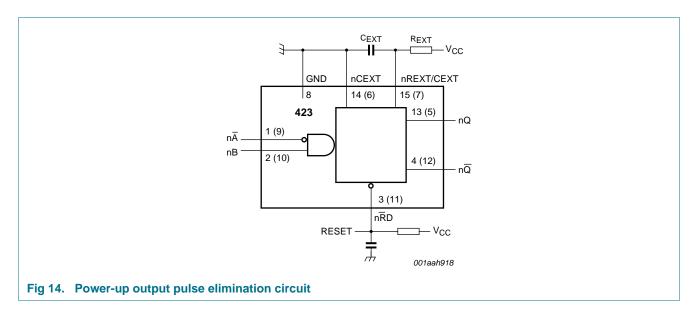
 t_W = pulse width in μs ;

 R_{EXT} = external resistor in $k\Omega$;

C_{EXT} = external capacitor in nF.

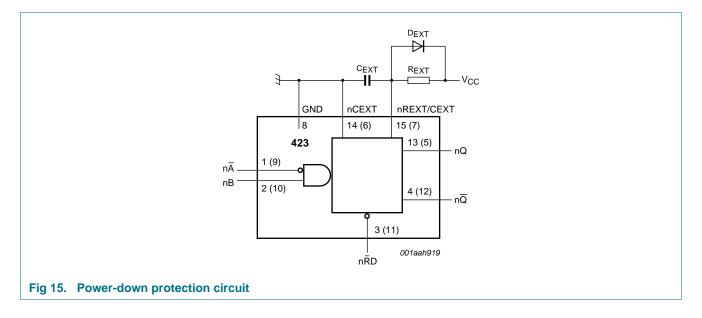
12.2 Power-up considerations

When the monostable is powered-up it may produce an output pulse, with a pulse width defined by the values of R_{EXT} and C_{EXT} , this output pulse can be eliminated using the circuit shown in Figure 14.



12.3 Power-down considerations

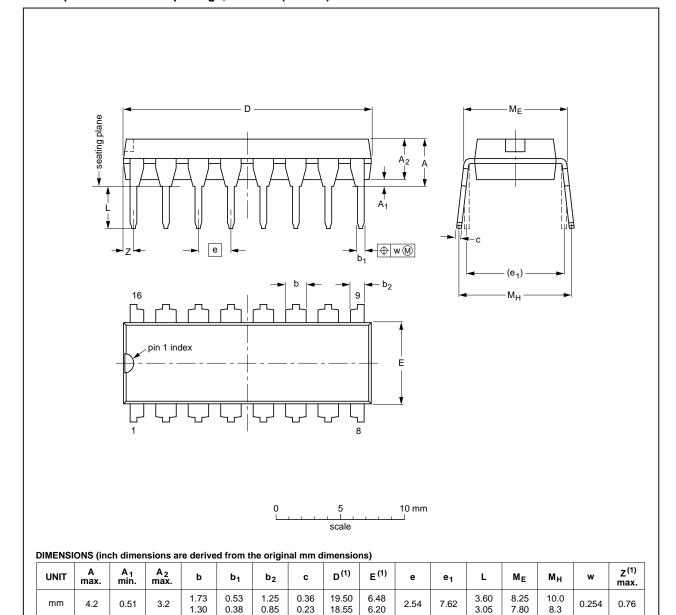
A large capacitor C_{EXT} may cause problems when powering-down the monostable due to the capacitor's stored energy. When a system containing this device is powered-down or a rapid decrease of V_{CC} to zero occurs, the monostable may sustain damage, due to the capacitor discharging through the input protection diodes. To avoid this possibility, use a damping diode D_{EXT} preferably a germanium or Schottky type diode able to withstand large current surges and connect as shown in Figure 15.



13. Package outline

DIP16: plastic dual in-line package; 16 leads (300 mil)

SOT38-4



Note

inches

0.17

1. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

0.015

0.068

0.051

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT38-4					95-01-14 03-02-13

0.77

0.26

0.1

0.14

0.32

Fig 16. Package outline SOT38-4 (DIP16)

0.02

0.13

74HC_HCT423

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0.01

0.03

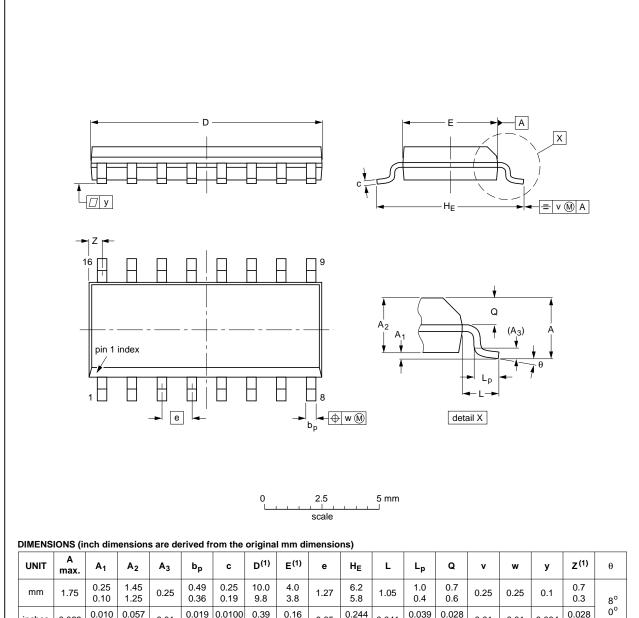
0.049

0.033

0.014

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	ø	v	w	у	Z ⁽¹⁾	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	10.0 9.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
inches	0.069	0.010 0.004	0.057 0.049	0.01		0.0100 0.0075	0.39 0.38	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.020	0.01	0.01	0.004	0.028 0.012	0°

Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT109-1	076E07	MS-012				99-12-27 03-02-19

Fig 17. Package outline SOT109-1 (SO16)

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DHVQFN16: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 x 3.5 x 0.85 mm SOT763-1

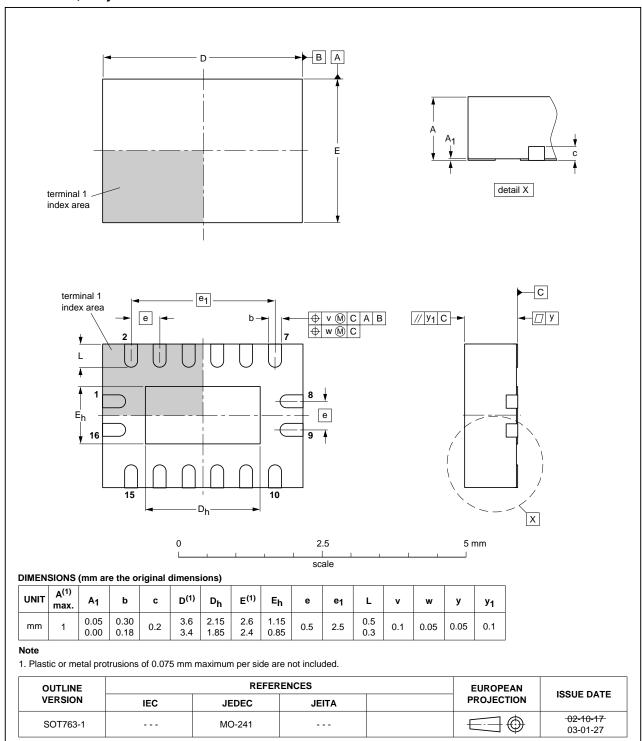
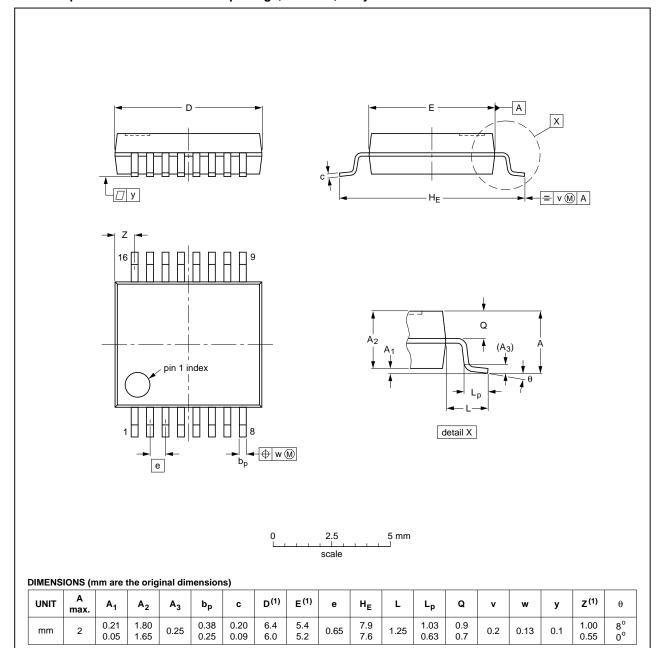


Fig 18. Package outline SOT763-1 (DHVQFN16)

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SSOP16: plastic shrink small outline package; 16 leads; body width 5.3 mm

SOT338-1



Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT338-1		MO-150			99-12-27 03-02-19	

Fig 19. Package outline SOT338-1 (SSOP16)

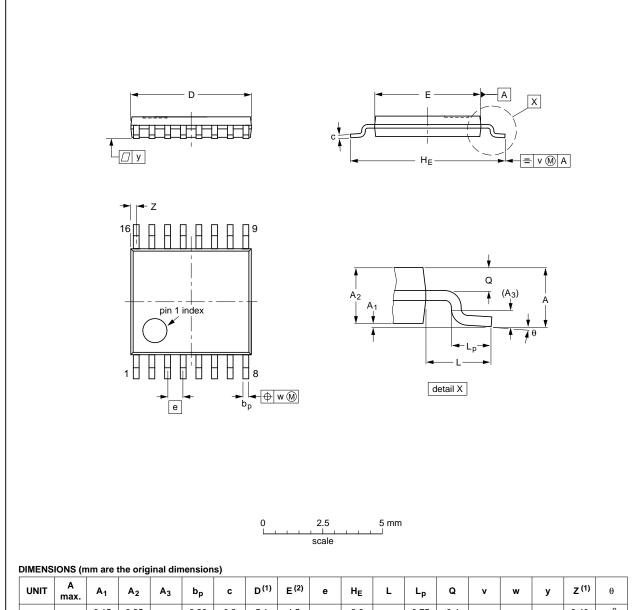
74HC_HCT423

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TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm

SOT403-1



UNIT	A max.	A ₁	A ₂	A ₃	b _p	С	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.40 0.06	8° 0°

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT403-1		MO-153			99-12-27 03-02-18

Fig 20. Package outline SOT403-1 (TSSOP16)

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14. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT423 v.6	20111219	Product data sheet	-	74HC_HCT423 v.5
Modifications:	 Legal page 	s updated.		
74HC_HCT423 v.5	20110825	Product data sheet	-	74HC_HCT423 v.4
74HC_HCT423 v.4	20110318	Product data sheet	-	74HC_HCT423 v.3
74HC_HCT423 v.3	20080724	Product data sheet	-	74HC_HCT423_CNV v.2
74HC_HCT423_CNV v.2	19980708	Product specification	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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74HC_HCT423

74HC423; 74HCT423

Dual retriggerable monostable multivibrator with reset

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